

ROITHNER LASERTECHNIK

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RLT6310G

TECHNICAL DATA



High Power Visible Wavelength Laserdiode

Structure: **AlGaInP**, index guided

Lasing wavelength: **635 nm**

Max. optical power: **10 mW**

Package: **9 mm**

NOTE!

**LASERDIODE
MUST BE COOLED!**

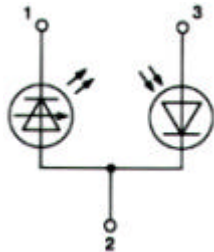


ATTENTION

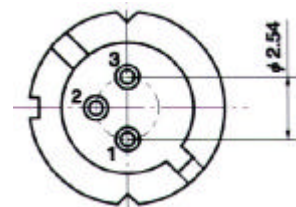
OBSERVE PRECAUTIONS
FOR HANDLING

ELECTROSTATIC SENSITIVE DEVICE

PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Maximum Ratings (T_c=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	10	mW
LD Reverse Voltage	V _{R(LD)}	2	V
PD Reverse Voltage	V _{R(PD)}	30	V
Operation Case Temperature	T _C	-10 .. +50	°C
Storage Temperature	T _{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P _o	kink free		10		mW
Threshold Current	I _{th}		45	60	80	mA
Operation Current	I _{op}	P _o = 10 mW		60	80	mA
Operating Voltage	V _{op}	P _o = 10 mW		2.2	2.5	V
Lasing Wavelength	λ _p	P _o = 10 mW		635	640	nm
Beam Divergence	θ _{//}	P _o = 10 mW	6	9	16	°
Beam Divergence	θ _⊥	P _o = 10 mW	25	31	37	°
Monitor Current	I _m	P _o = 10 mW, V _r = 5V	10	100		μA
Astigmatism	A _s	P _o = 10 mW		11		μm